

SANYO	No.2473A	2 S C 4 1 0 8
		NPN Triple Diffused Planar Type Silicon Transistor
SWITCHING REGULATOR APPLICATIONS		

Features

- . High breakdown voltage and high reliability
- . Fast switching speed
- . Wide ASO
- . Adoption of MBIT process

Absolute Maximum Ratings at Ta=25°C

			unit
Collector-to-Base Voltage	V _{CB0}	500	V
Collector-to-Emitter Voltage	V _{CEO}	400	V
Emitter-to-Base Voltage	V _{EBO}	7	V
Collector Current	I _C	12	A
Peak Collector Current	i _{cp}	PW ≤ 300μs, duty cycle ≤ 10%	25 A
Base Current	I _B	4	A
Collector Dissipation	P _C	Tc=25°C	2.5 W
Junction Temperature	T _j		100 W
Storage Temperature	T _{stg}		150 °C
			-55 to +150 °C

Electrical Characteristics at Ta=25°C

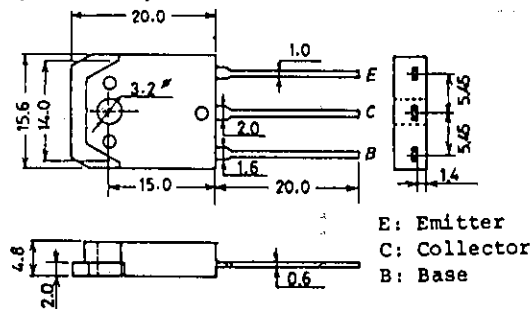
			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} =400V, I _E =0			10	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0			10	μA
DC Current Gain	h _{FE} (1)	V _{CE} =5V, I _C =1.6A	15*		50*	
	h _{FE} (2)	V _{CE} =5V, I _C =8A	10			
	h _{FE} (3)	V _{CE} =5V, I _C =10mA	10			
C-E Saturation Voltage	V _{CE(sat)}	I _C =8A, I _B =1.6A			0.8	V
B-E Saturation Voltage	V _{BE(sat)}	I _C =8A, I _B =1.6A			1.5	V
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =1.6A		20		MHz
Output Capacitance	c _{ob}	V _{CB} =10V, f=1MHz		160		pF

Continued on next page.

*: The h_{FE1} of the 2SC4108 is classified as follows. When specifying the h_{FE1} rank, specify two ranks or more in principle.

15	L	30	20	M	40	30	N	50
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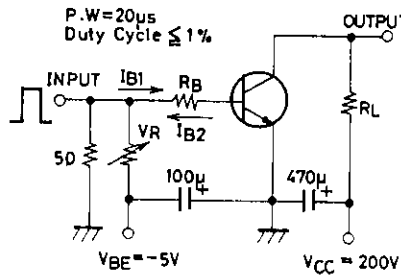
Package Dimensions 2022
(unit: mm)



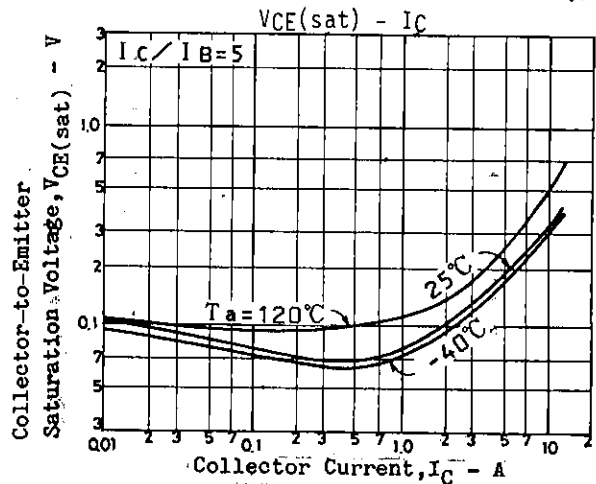
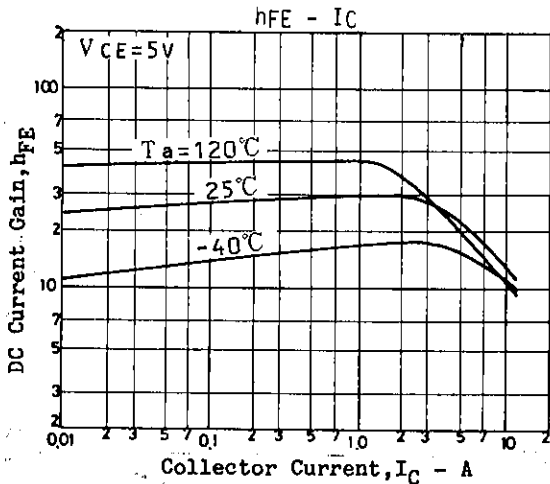
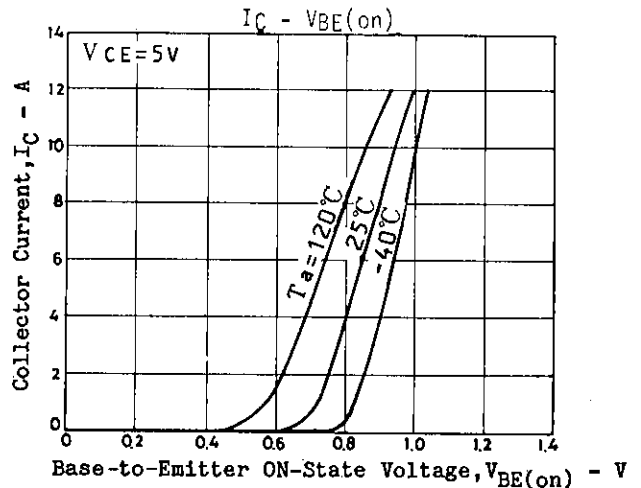
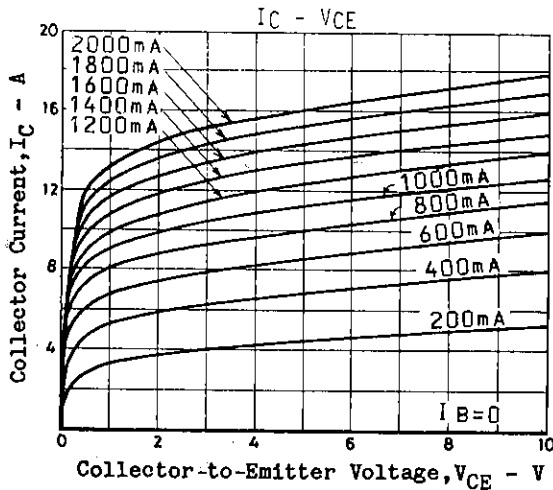
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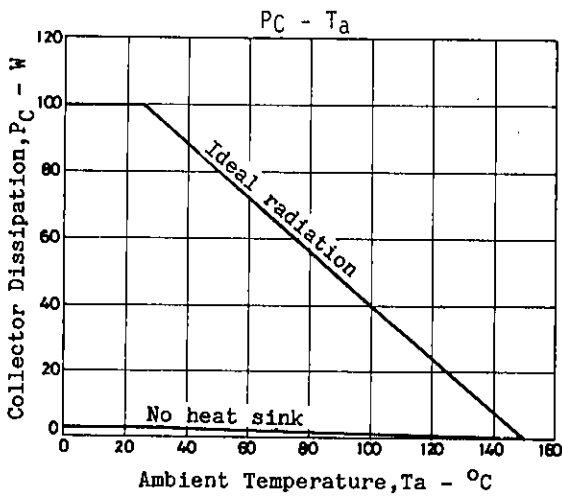
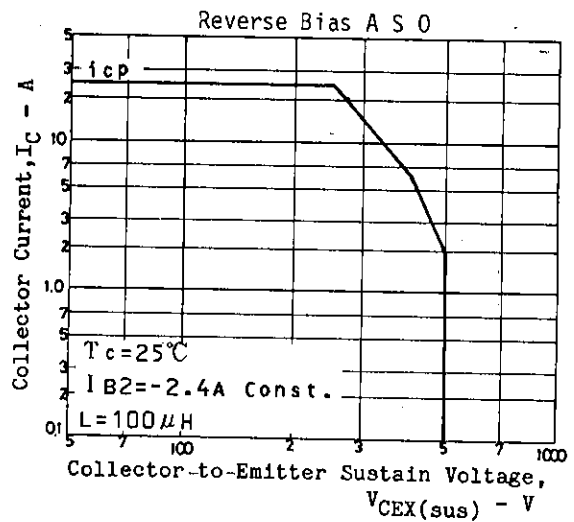
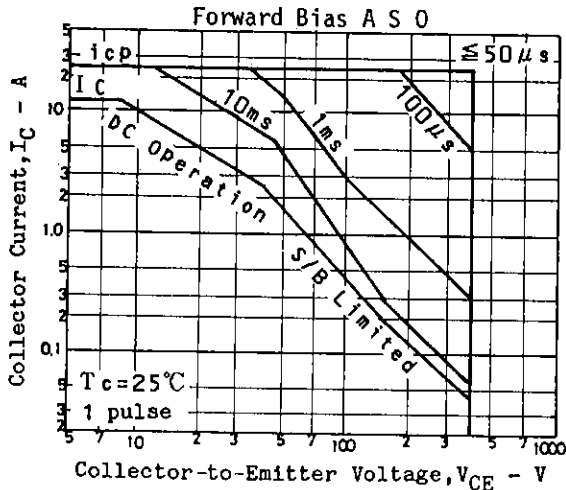
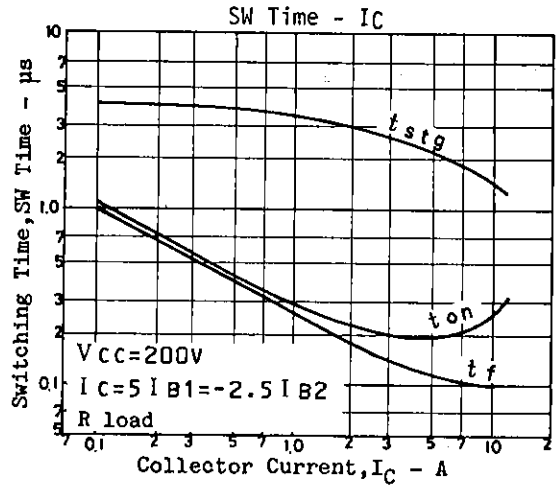
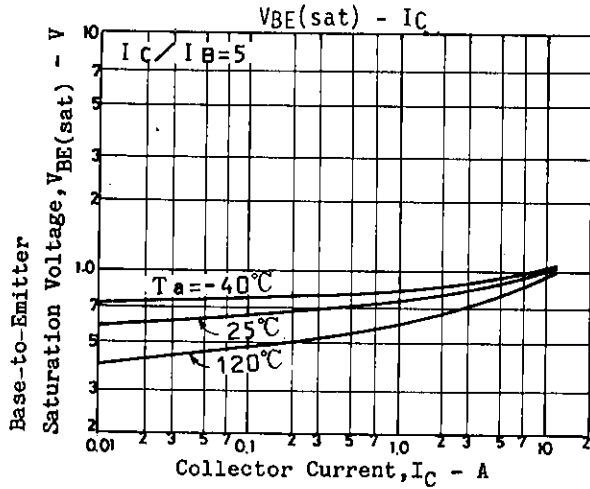
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	400			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
C-E Sustain Voltage	$V_{CEX(sus)}$	$I_C=6A, I_{B1}=0.6A,$ $I_{B2}=-2.4A, L=500\mu H,$ clamped	400			V
Turn-on Time	t_{on}	$I_C=10A, I_{B1}=2A,$ $I_{B2}=-4A, R_L=20ohms,$ $V_{CC}=200V$			0.5	μs
Storage Time	t_{stg}	$I_C=10A, I_{B1}=2A,$ $I_{B2}=-4A, R_L=20ohms,$ $V_{CC}=200V$			2.5	μs
Fall Time	t_f	$I_C=10A, I_{B1}=2A,$ $I_{B2}=-4A, R_L=20ohms,$ $V_{CC}=200V$			0.3	μs

Switching Time Test Circuit



Unit (Resistance : Ω , Capacitance : F)





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